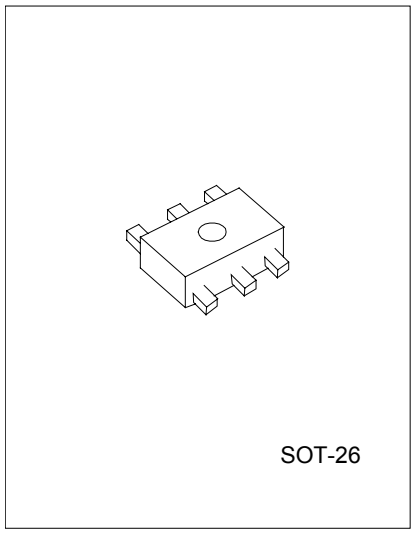
GENERAL PURPOSE DUAL TRANSISTOR

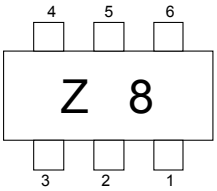
FEATURES
*Both a 8550S chip and 8050S chip in a SMT package

APPLICATIONS
*Class B push-pull audio amplifier
*General purpose applications

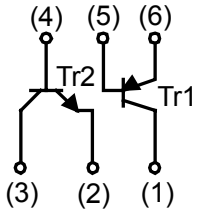


PIN 1 : Collector (1) PIN 4: Base (2)
PIN 2: Emitter (2) PIN 5: Base (1)
PIN 3: Collector (2) PIN 6: Emitter (1)

MARKING



EQUIVALENT CIRCUITS



ABSOLUTE MAXIMUM RATINGS (Ta=25°C ,unless otherwise specified)

PARAMETER	SYMBOL	RATING		UNIT
		Tr1	Tr2	
Collector-Base Voltage	V_{CBO}	-30	30	V
Collector-Emitter Voltage	V_{CEO}	-20	20	V
Emitter-Base Voltage	V_{EBO}	-5	5	V
Collector Current	Ic	-700	700	mA
Collector Dissipation	Pc	300		mW
Junction Temperature	T_j	150		°C
Storage Temperature	T_{STG}	-65 ~ +150		°C

ELECTRICAL CHARACTERISTICS (Ta=25°C,unless otherwise specified)

Tr1

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	BV_{CBO}	Ic=-100μA,I_E=0	-30			V
Collector-emitter breakdown voltage	BV_{CEO}	Ic=-1mA,I_B=0	-20			V
Emitter-base breakdown voltage	BV_{EBO}	I_E=-100μA,Ic=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-30V,I_E=0			-1	uA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,Ic=0			-100	nA
DC current gain	hFE_1	V_{CE}=-1V,Ic=-1mA	100			
	hFE2	V_{CE}=-1V,Ic=-150mA	120	110	400	

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	hFE3	V_{CE}=-1V,I_C=-500mA	40			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-500mA,I_B=-50mA			-0.5	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=500mA,I_B=-50mA			-1.2	V
Base-emitter saturation voltage	V_{BE}	V_{CE}=-1V,I_C=-10mA			-1.0	V
Current gain bandwidth product	f_T	V_{CE}=-10V,I_C=-50mA	100			MHz
Output capacitance	Cob	V_{CB}=10V,I_E=0,f=1MHz		9.0		pF

Tr2

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=100μA,I_E=0	30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=1mA,I_B=0	20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=100μA,I_C=0	5			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=30V,I_E=0			1	uA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5V,I_C=0			100	nA
DC Current Gain	h_{FE1}	V_{CE}=1V,I_C=1mA	100			
	hFE2	V_{CE}=1V,I_C=150mA	120	110	400	
	hFE3	V_{CE}=1V,I_C=500mA	40			
Collector-Emitter Saturation Voltage	V_{CE}(sat)	I_C=500mA,I_B=50mA			0.5	V
Base-Emitter Saturation Voltage	V_{BE}(sat)	I_C=500mA,I_B=50mA			1.2	V
Base-Emitter Saturation Voltage	V_{BE}	V_{CE}=1V,I_C=10mA			1.0	V
Current Gain Bandwidth Product	f_T	V_{CE}=10V,I_C=50mA	100			MHz
Output Capacitance	Cob	V_{CB}=10V,I_E=0,f=1MHz		9.0		pF

CLASSIFICATION OF hFE2

RANK	C	D	E
RANGE	120-200	160-300	280-400